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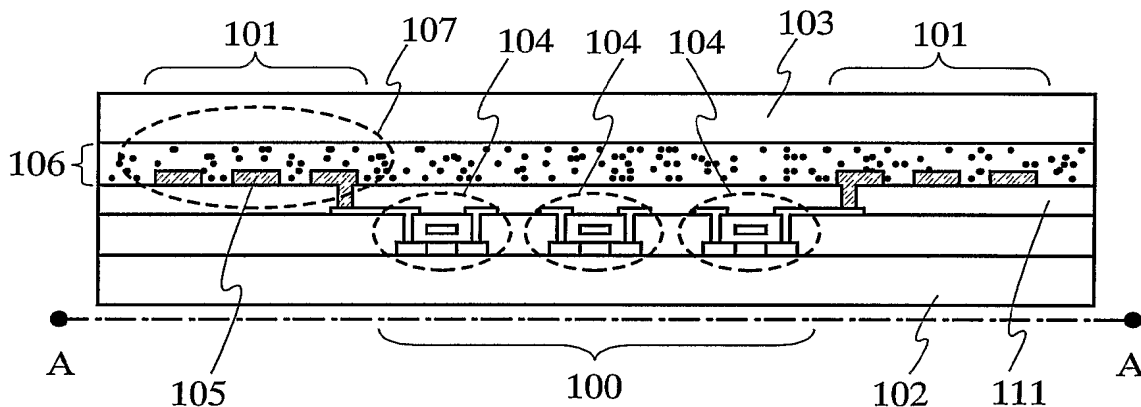
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(54) Title: SEMICONDUCTOR DEVICE



(57) Abstract: A semiconductor device such as an ID chip of the present invention includes an integrated circuit using a semiconductor element formed by using a thin semiconductor film, and an antenna connected to the integrated circuit. It is preferable that the antenna is formed integrally with the integrated circuit, since the mechanical strength of an ID chip can be enhanced. Note that the antenna used in the present invention also includes a conducting wire that is wound round circularly or spirally and fine particles of a soft magnetic material are arranged between the conducting wires. Specifically, an insulating layer in which fine particles of a soft magnetic material are arranged between the conducting wires. Specifically, an insulating layer in which fine particles of a soft magnetic material are included is arranged between the conducting wires.

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